





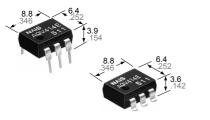




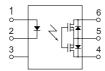
Panasonic ideas for life

General use and economy type. DIP (1 Form B) 6-pin type. Reinforced insulation 5,000V type.

hotoMOS



mm inch



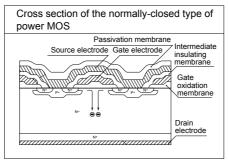
2. This is the low-cost version PhotoMOS 1 Form B output type relay.

Compared to the previous GU PhotoMOS 1 Form B type relay, the attainment of an economical price that is approximately 22% lower will further broaden its market.

3. Normally closed type (2 Form B) is low on-resistance.

(All AQO4 PhotoMOS are Form B types. And also the Form A types have a low on-resistance.)

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Doublediffused and Selective Doping) method.



4. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, low ON resistance

Can control a maximum 0.13 A load current with a 5 mA input current. Low ON resistance of 18 Ω (AQV410EH). Stable operation because there are no metallic contact parts.

6. Low-level off-state leakage current

The SSR has an off-state leakage current of several milliamperes, whereas the PhotoMOS relay has typ. 100 pA even with the rated load voltage of 400 V (AQV414E).

7. Reinforced insulation 5,000 V type also available.

More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

TYPICAL APPLICATIONS

- Power supply
- Measuring equipment
- Security equipment
- Telephone equipment
- Sensors

FEATURES

1. 60V type couples high capacity (0.55A) with low on-resistance (1 Ω).

Item	GU-E (1 Form B type) type					
Part No.	AQV410EH	AQV412EH				
Load voltage	350V	60V				
Continuous load current	0.13A	0.55A				
ON resistance (typ.)	18Ω	1Ω				

TYPES

IVDE		Output rating*			Pa	Packing quantity			
	I/O isolation voltage			Through hole terminal	S				
			Lood			Tape and reel packing style			
		Load voltage	Load	Tube pac	king style	Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	Tape and reel
-,	400 V	120 mA	AQV414E	AQV414EA	AQV414EAX	AQV414EAZ	1 tube contains		
	5,000 V AC (Reinforced)	350 / 130		AQV412EH	AQV412EHA	AQV412EHAX	AQV412EHAZ	50 pcs. 1 batch contains	1,000 pcs.
				AQV410EH AQV410EHA		AQV410EHAX	AQV410EHAZ	500 pcs.	
		400 V	120 mA	AQV414EH	AQV414EHA	AQV414EHAX	AQV414EHAZ	000 poo.	

^{*}Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

GU-E PhotoMOS (AQV414E, AQV41OEH)

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

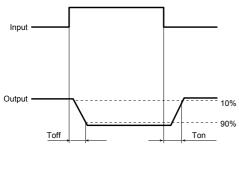
Item		Symbol	Type of connection	AQV414E(A)	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Remarks
	LED forward current	lF			50			
	LED reverse voltage	VR			5			
Input	Peak forwrd current	I FP		1 A f		f = 100 Hz, Duty factor = 0.1%		
	Power dissipation	Pin		75 mW				
	Load voltage (peak AC)	VL		400 V	60 V	350 V	400 V	
	Continuous load current	lι	Α	0.12 A	0.55 A	0.13 A	0.12 A	A server tiene Beels AO BO
Output			В	0.13 A	0.65 A	0.15 A	0.13 A	A connection: Peak AC, DC B,C connection: DC
			С	0.15 A	0.8 A	0.17 A	0.15 A	
	Peak load current	Ipeak		0.3 A	1.5 A	0.4 A	0.3 A	A connection: 100 ms (1 shot), V _L = DC
	Power dissipation	Pout		500 mW				
Total power dissipation		Рт		550 mW				
I/O isolation voltage		Viso		1,500 V AC	5,000 V AC			
limits	Operating	Topr		-40°C to +85°C -40°F to +185°F				Non-condensing at low temperatures
	Storage T _{stg}			-40°C to +100°C -40°F to +212°F				

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	Type of connection	AQV414E(A)	AQV412EH(A)	AQV410EH(A)	AQV414EH(A)	Condition		
	LED operate (OFF) current		Typical Maximum	Foff	_	1.45 mA 1.9 mA 1.9 mA 1.9 mA			IL= Max.		
Input	LED reverse (ON)		Minimum			3.0 mA 0.3 mA 0.4 mA 0.4 mA 0.4 mA					
				I Fon			-			IL= Max.	
	Current		Typical			1.40 mA					
	LED dropo	ut voltage	Typical	VF	_	1.25 V (1.14 V at I⊧= 5 mA)				I⊧= 50 mA	
			Maximum					5 V		50 110 1	
	On resistance		Typical	Ron	A	26 Ω	1 Ω	18 Ω	25.2 Ω	I _F = 0 mA I _L = Max. Within 1 s on time	
			Maximum			50 Ω	2.5 Ω	35 Ω	50 Ω		
			Typical	Ron	В	20 Ω	0.55 Ω	13 Ω	19 Ω	I _F = 0 mA I _L = Max. Within 1 s on time	
Output			Maximum			25 Ω	1.3 Ω	17.5 Ω	25 Ω		
			Typical	Ron	С	10 Ω	0.3 Ω	6.5 Ω	10 Ω	I _F = 0 mA I _L = Max. Within 1 s on time	
			Maximum			12.5 Ω	0.7 Ω	8.8 Ω	12.5 Ω		
	Off state leakage current		Maximum	Leak	_	1 μΑ	10 μΑ	10 μΑ	10 μΑ	I⊧= 5 mA V∟ = Max.	
	Switching speed	Operate (OFF) time*	Typical	Toff	_	0.7 ms	3 ms	1.5 ms	1.3 ms	$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}$ $I_L = \text{Max}.$	
Transfer characteristics			Maximum			2.0 ms	10 ms	3.0 ms	3.0 ms		
		Reverse (ON) time*	Typical	_	_	0.1 ms	0.3 ms	0.3 ms	0.3 ms	I _F = 5 mA → 0 mA	
			Maximum	Ton		1.0 ms	1.5 ms	1.5 ms	1.5 ms	I∟ = Max.	
	I/O capacitance		Typical	Ciso	_	0.8 pF				f = 1 MHz V _B = 0 V	
			Maximum			1.5 pF					
	Initial I/O isolation resistance		Minimum	Riso	_	1,000 ΜΩ			500 V DC		

Note: Recommendable LED forward current

Standard type I_F = 5 mA Reinforced type I_F = 5 to 10 mA *Operate/Reverse time

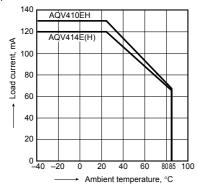


REFERENCE DATA

1-(1). Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to +85°C -40°F to +185°F

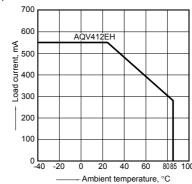
Type of connection: A



1-(2). Load current vs. ambient temperature characteristics

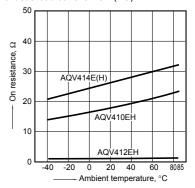
Allowable ambient temperature: -40°C to +85°C -40°F to +185°F

Type of connection: A



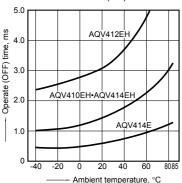
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6: LED current: 0 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



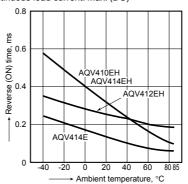
3. Operate (OFF) time vs. ambient temperature

LED current: 5mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



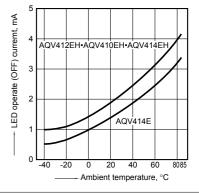
4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



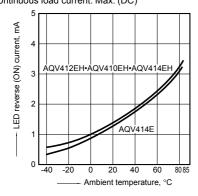
5. LED operate (OFF) current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)

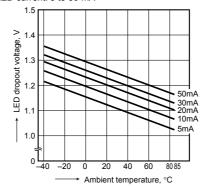


6. LED reverse (ON) current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)

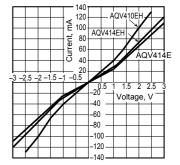


7. LED dropout voltage vs. ambient temperature characteristics Sample: All types; LED current: 5 to 50 mA



8-(1). Current vs. voltage characteristics of output at MOS portion

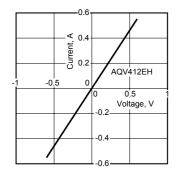
. Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



GU-E PhotoMOS (AQV414E, AQV41OEH)

8-(2). Current vs. voltage characteristics of output at MOS portion

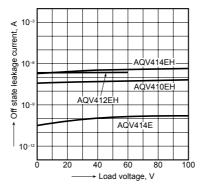
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C $77^{\circ}F$



9. Off state leakage current vs. load voltage characteristics

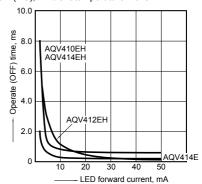
Sample: All types;

Measured portion: between terminals 4 and 6; LED current: 5 mA; Ambient temperature: 25°C 77°F



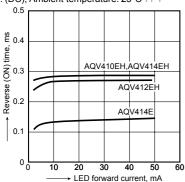
10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77° F



11. Reverse (ON) time vs. LED forward current characteristics

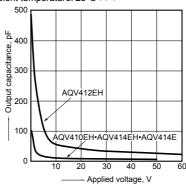
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: $25^{\circ}C$ $77^{\circ}F$



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6;

Frequency: 1 MHz; Ambient temperature: 25°C 77°F



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